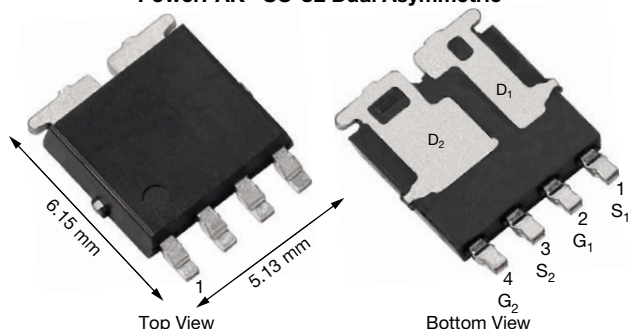


Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFETs

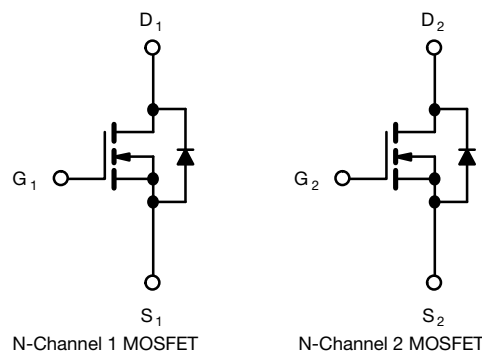
PowerPAK® SO-8L Dual Asymmetric


FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Optimized for synchronous buck applications
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY		
	N-CHANNEL 1	N-CHANNEL 2
V_{DS} (V)	40	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.00940	0.00390
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.01173	0.00480
I_D (A)	20	60
Configuration	Dual	
Package	PowerPAK SO-8L asymmetric	



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER			SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Drain-source voltage			V _{DS}	40	40	V
Gate-source voltage			V _{GS}	± 20		
Continuous drain current	T _C = 25 °C		I _D	20 ^a	60 ^a	A
	T _C = 125 °C			20 ^a	46	
Continuous source current (diode conduction)			I _S	20 ^a	44	
Pulsed drain current ^b			I _{DM}	80	220	
Single pulse avalanche current	L = 0.1 mH		I _{AS}	18	29	
Single pulse avalanche energy			E _{AS}	16	42	mJ
Maximum power dissipation ^b	T _C = 25 °C		P _D	27	48	W
	T _C = 125 °C			9	16	
Operating junction and storage temperature range			T _J , T _{stg}	-55 to +175		°C
Soldering recommendations (peak temperature) ^{d, e}				260		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT	
Junction-to-ambient	R_{thJA}	85	85	°C/W	
Junction-to-case (drain)	R_{thJC}	5.5	3.1		

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT
Static								
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		N-Ch 1	40	-	-	V
		V _{GS} = 0 V, I _D = 250 μA		N-Ch 2	40	-	-	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		N-Ch 1	1.3	1.8	2.3	
		V _{DS} = V _{GS} , I _D = 250 μA		N-Ch 2	1.4	1.9	2.4	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		N-Ch 1	-	-	± 100	nA
				N-Ch 2	-	-	± 100	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V	N-Ch 1	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 40 V	N-Ch 2	-	-	1	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	N-Ch 1	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	N-Ch 2	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	N-Ch 1	-	-	250	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	N-Ch 2	-	-	300	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	N-Ch 1	10	-	-	A
		V _{GS} = 10 V	V _{DS} ≥ 5 V	N-Ch 2	20	-	-	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 6 A	N-Ch 1	-	0.00770	0.00940	Ω
		V _{GS} = 10 V	I _D = 10 A	N-Ch 2	-	0.00320	0.00390	
		V _{GS} = 10 V	I _D = 6 A, T _J = 125 °C	N-Ch 1	-	-	0.01370	
		V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	N-Ch 2	-	-	0.00570	
		V _{GS} = 10 V	I _D = 6 A, T _J = 175 °C	N-Ch 1	-	-	0.01600	
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	N-Ch 2	-	-	0.00670	
		V _{GS} = 4.5 V	I _D = 4 A	N-Ch 1	-	0.00970	0.01173	
		V _{GS} = 4.5 V	I _D = 8 A	N-Ch 2	-	0.00400	0.00480	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 6 A		N-Ch 1	-	32	-	S
		V _{DS} = 15 V, I _D = 10 A		N-Ch 2	-	51	-	
Dynamic ^b								
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 1	-	1197	1700	pF
		V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 2	-	2839	3900	
Output capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 1	-	331	500	
		V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 2	-	888	1250	
Reverse transfer capacitance	C _{rss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 1	-	31	50	
		V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	N-Ch 2	-	27	40	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 1 A	N-Ch 1	-	22	33	nC
		V _{GS} = 10 V	V _{DS} = 20 V, I _D = 1 A	N-Ch 2	-	48.2	75	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 1 A	N-Ch 1	-	3.5	-	
		V _{GS} = 10 V	V _{DS} = 20 V, I _D = 1 A	N-Ch 2	-	7.1	-	
Gate-drain charge ^c	Q _{gd}	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 1 A	N-Ch 1	-	3.9	-	
		V _{GS} = 10 V	V _{DS} = 20 V, I _D = 1 A	N-Ch 2	-	8	-	
Gate resistance	R _g	f = 1 MHz		N-Ch 1	1.74	3.49	5.30	Ω
				N-Ch 2	0.55	1.10	1.65	

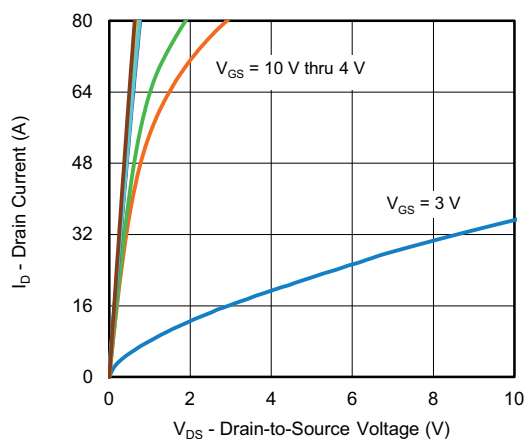
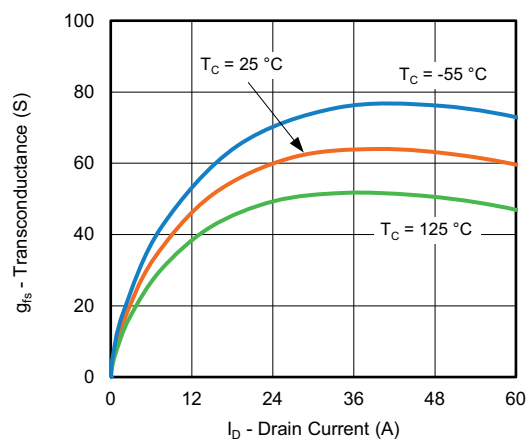
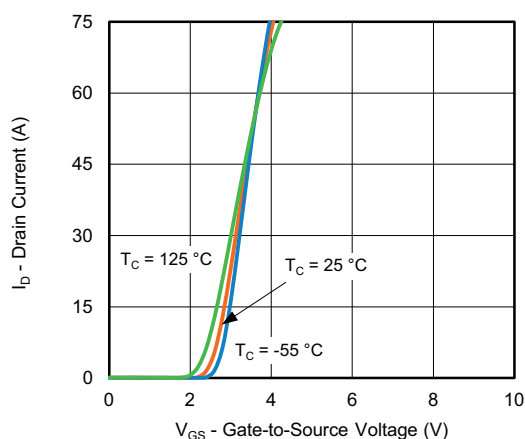
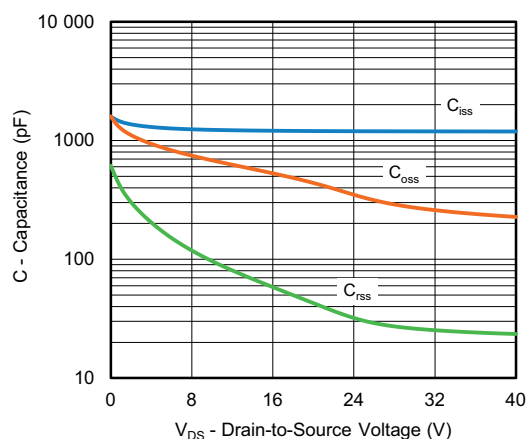
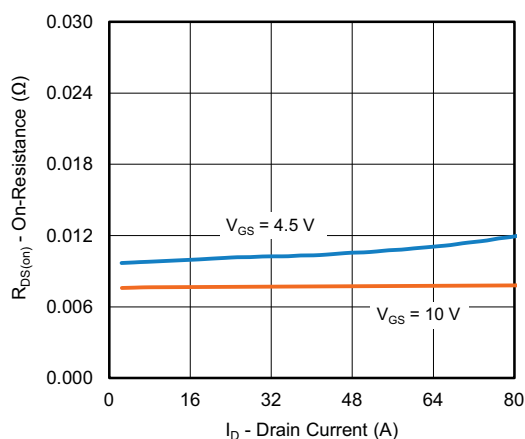
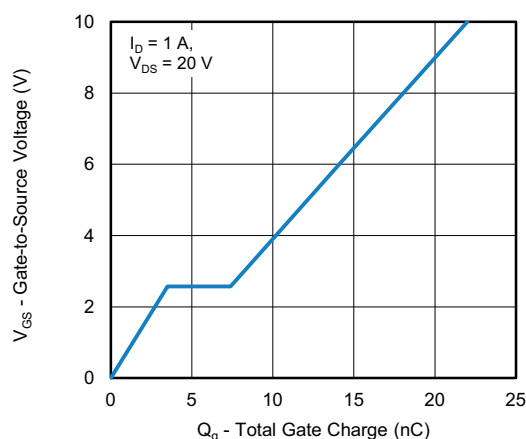


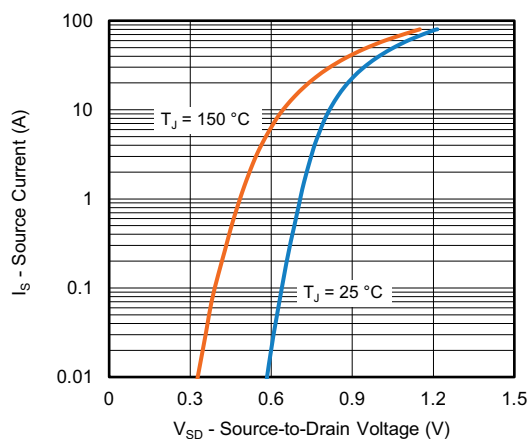
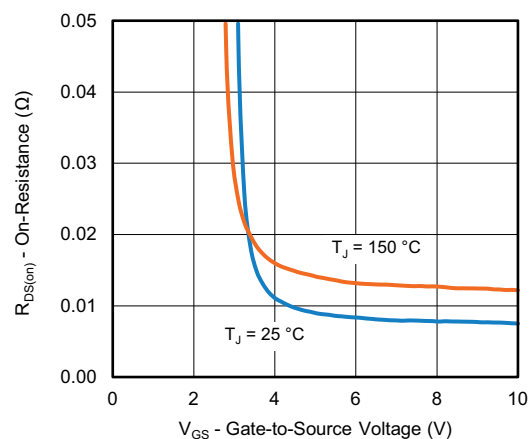
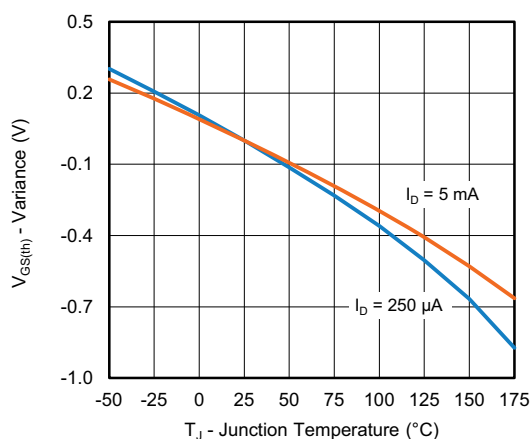
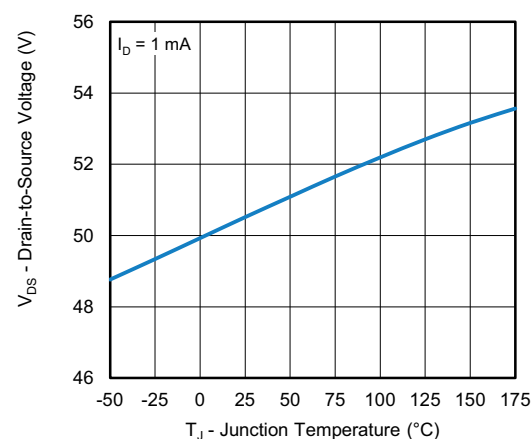
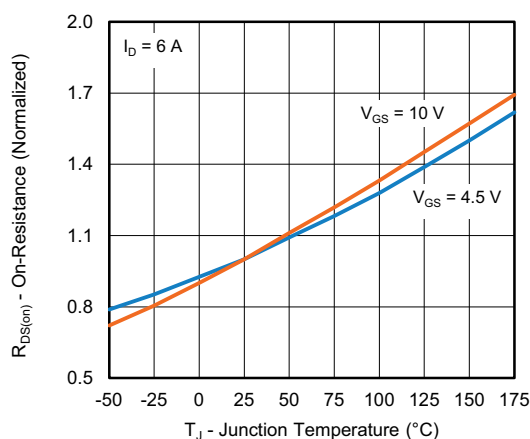
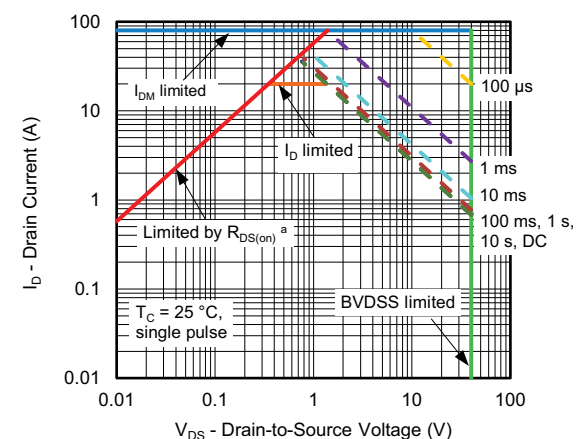
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Dynamic ^b							
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 20 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	10	20	ns
		V _{DD} = 20 V, R _L = 20 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	14	25	
Rise time ^c	t _r	V _{DD} = 20 V, R _L = 20 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	4	10	
		V _{DD} = 20 V, R _L = 20 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	5	10	
Turn-off delay time ^c	t _{d(off)}	V _{DD} = 20 V, R _L = 20 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	24	50	
		V _{DD} = 20 V, R _L = 20 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	35	55	
Fall time ^c	t _f	V _{DD} = 20 V, R _L = 20 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 1	-	25	50	
		V _{DD} = 20 V, R _L = 20 Ω, I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 1 Ω	N-Ch 2	-	57	90	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}		N-Ch 1	-	-	80	A
			N-Ch 2	-	-	220	
Forward voltage	V _{SD}	I _F = 6 A, V _{GS} = 0 V	N-Ch 1	-	0.77	1.2	V
		I _F = 10 A, V _{GS} = 0 V	N-Ch 2	-	0.76	1.2	
Body diode reverse recovery time	t _{rr}	I _F = 1 A, di/dt = 100 A/μs	N-Ch 1	-	28	60	ns
		I _F = 1 A, di/dt = 100 A/μs	N-Ch 2	-	39	80	
Body diode reverse recovery charge	Q _{rr}	I _F = 1 A, di/dt = 100 A/μs	N-Ch 1	-	17	35	nC
		I _F = 1 A, di/dt = 100 A/μs	N-Ch 2	-	46	95	
Reverse recovery fall time	t _a	I _F = 1 A, di/dt = 100 A/μs	N-Ch 1	-	14	-	ns
		I _F = 1 A, di/dt = 100 A/μs	N-Ch 2	-	23	-	
Reverse recovery rise time	t _b	I _F = 1 A, di/dt = 100 A/μs	N-Ch 1	-	14	-	
		I _F = 1 A, di/dt = 100 A/μs	N-Ch 2	-	16	-	
Body diode peak reverse recovery current	I _{RM(REC)}	I _F = 1 A, di/dt = 100 A/μs	N-Ch 1	-	-1.1	-	A
		I _F = 1 A, di/dt = 100 A/μs	N-Ch 2	-	-2.1	-	

Notes

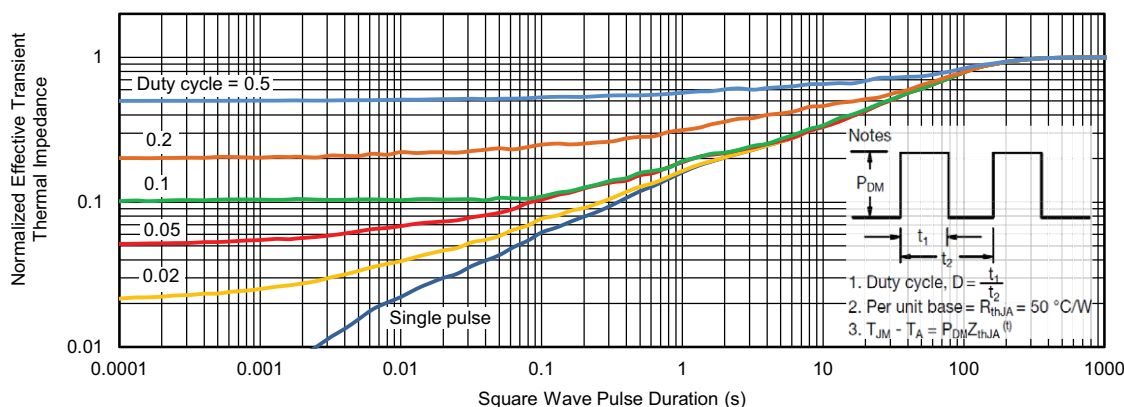
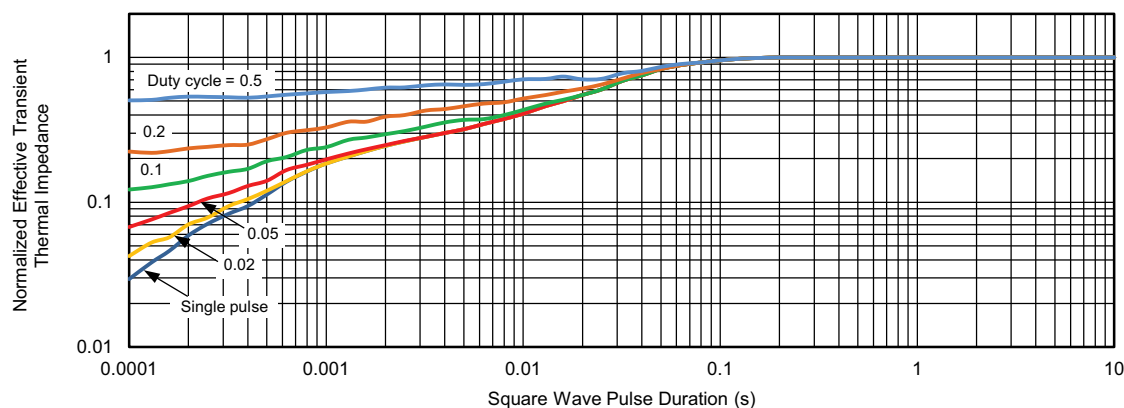
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

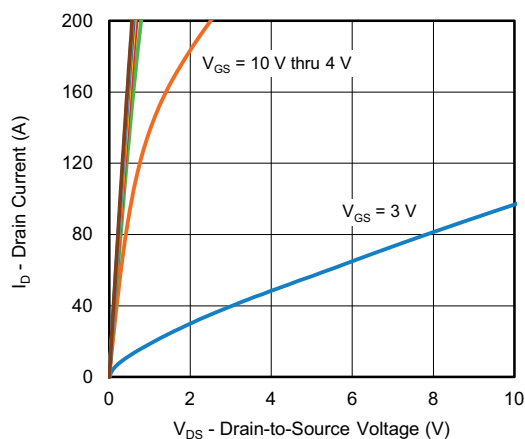
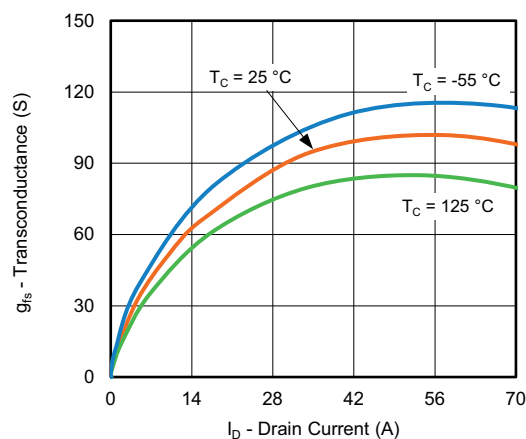
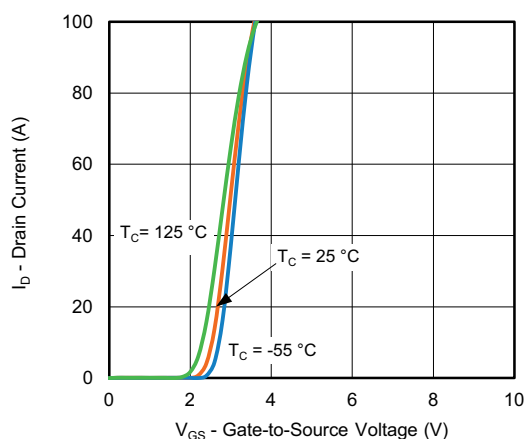
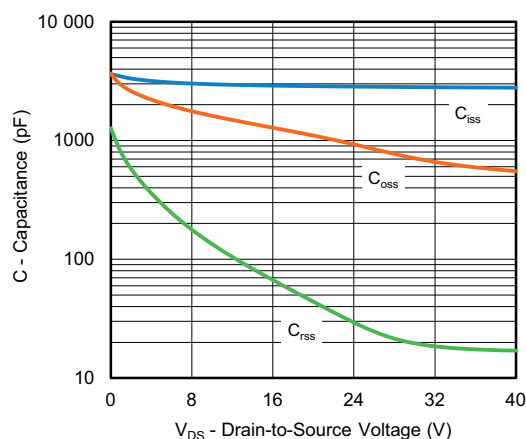
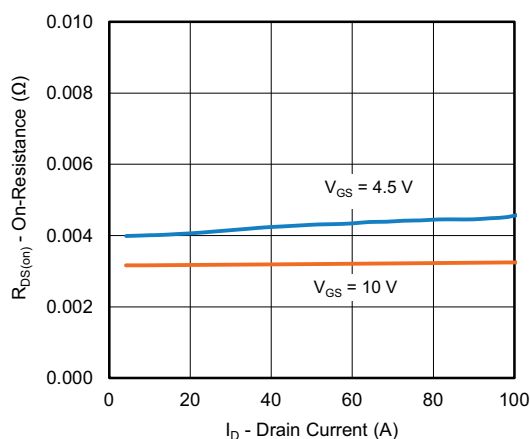
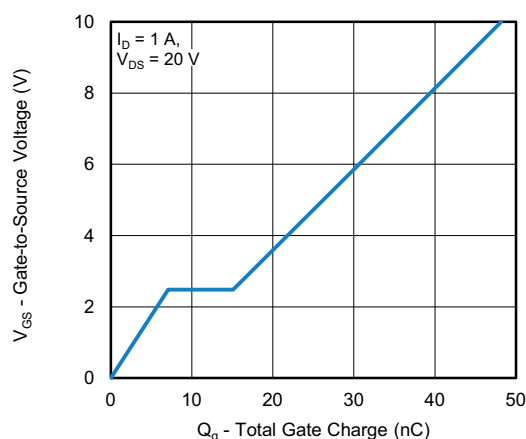
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transconductance

Transfer Characteristics

Capacitance

On-Resistance vs. Drain Current

Gate Charge

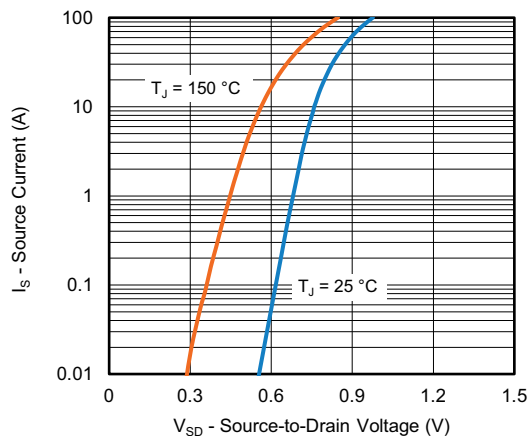
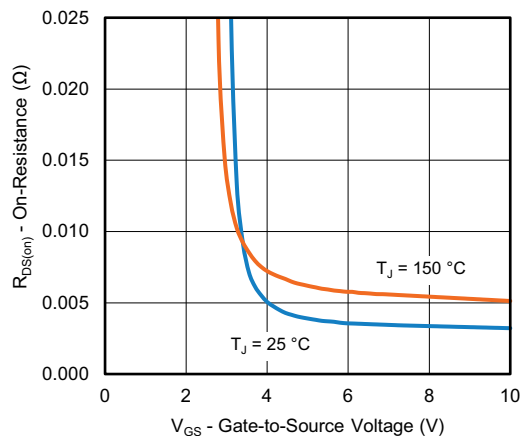
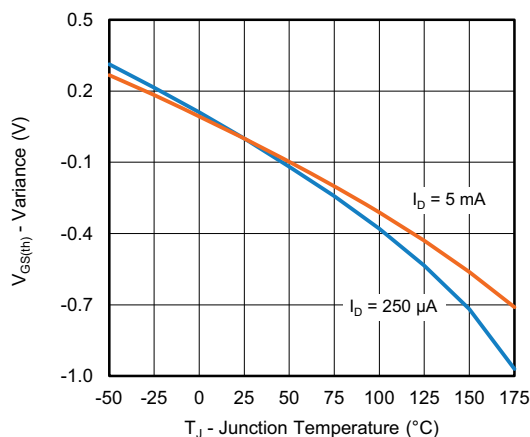
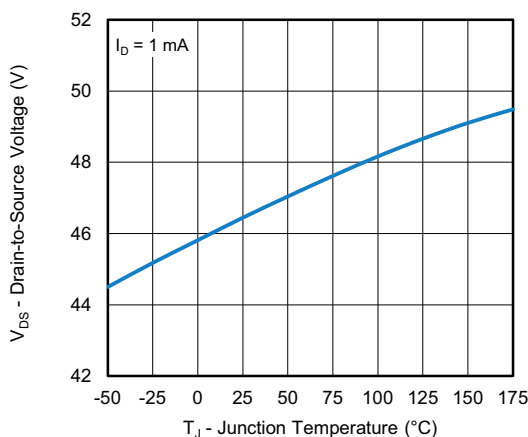
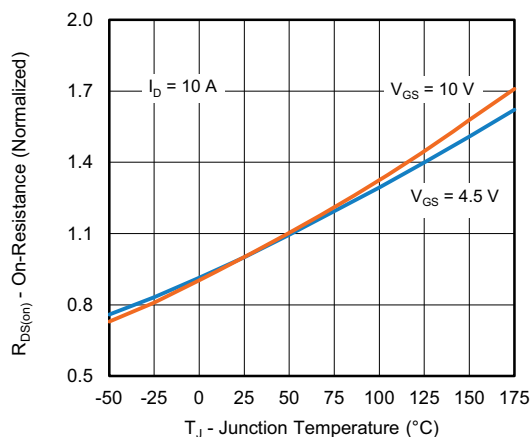
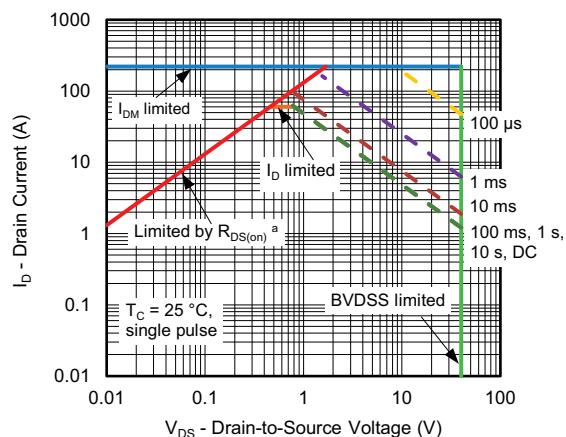
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

On-Resistance vs. Junction Temperature

Safe Operating Area
Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

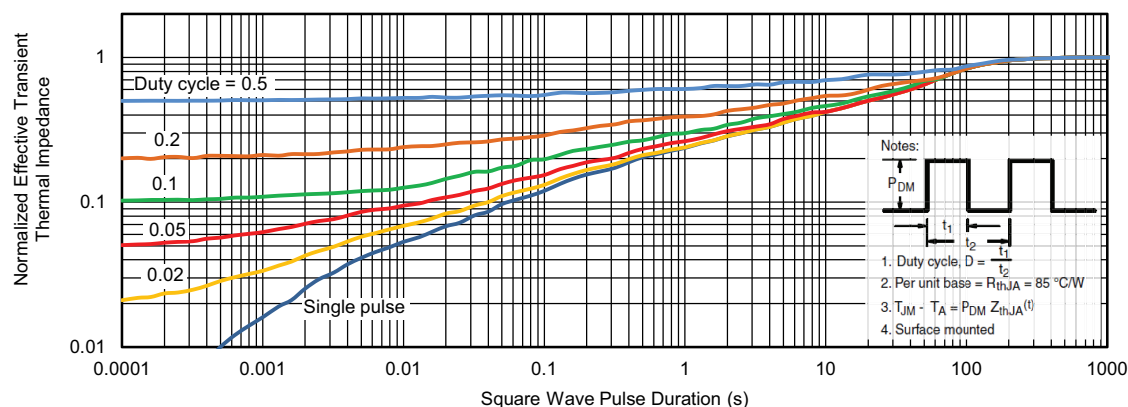
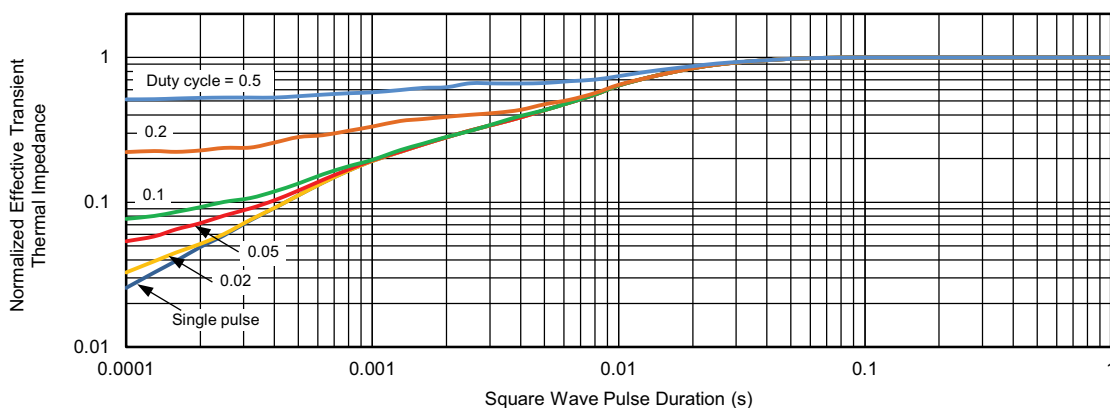
N-CHANNEL 1 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 is given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transconductance

Transfer Characteristics

Capacitance

On-Resistance vs. Drain Current

Gate Charge

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

On-Resistance vs. Junction Temperature

Safe Operating Area
Note

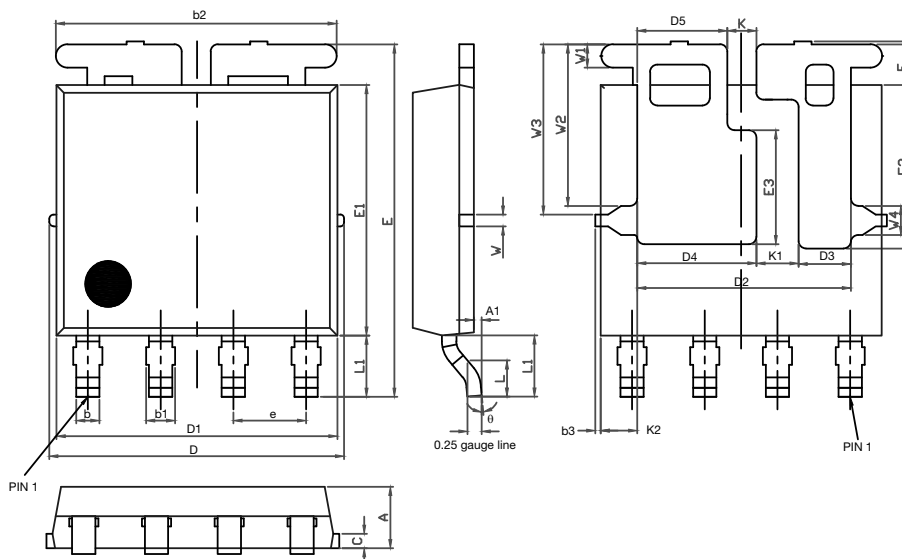
- a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

N-CHANNEL 2 TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case
Note

- The characteristics shown in the graph:
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77836.

PowerPAK® SO-8L Assymmetric Case Outline



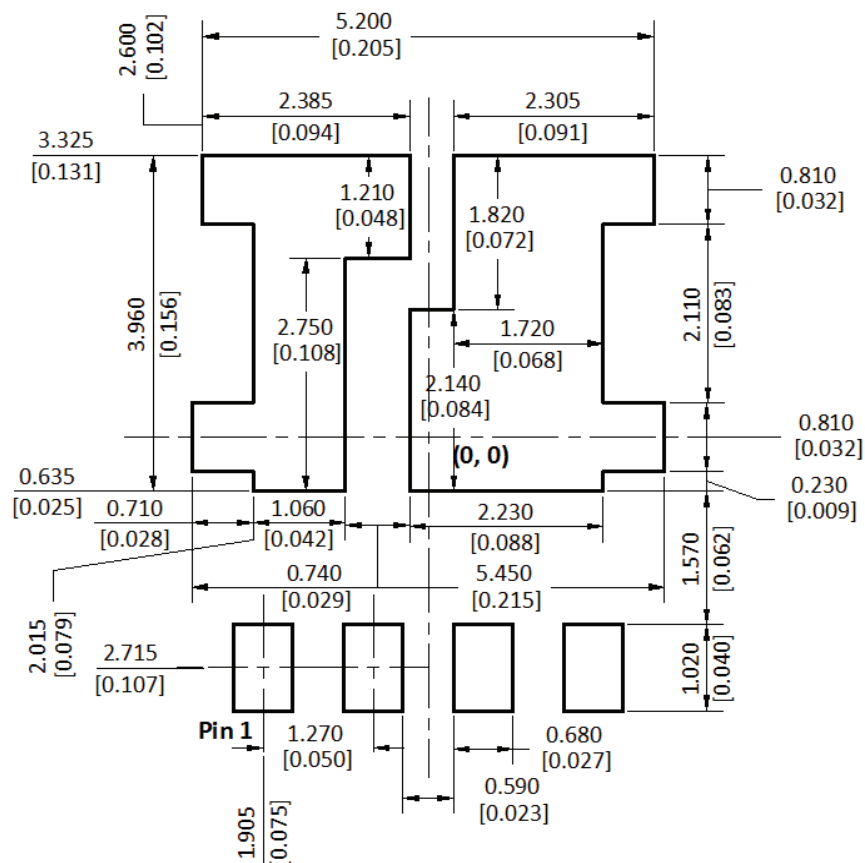
DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	0.06	0.13	0.000	0.003	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.04	0.12	0.20	0.002	0.005	0.008
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.63	3.73	3.83	0.143	0.147	0.151
D3	0.81	0.91	1.01	0.032	0.036	0.040
D4	1.98	2.08	2.18	0.078	0.082	0.086
D5	1.47	1.57	1.67	0.058	0.062	0.066
e	1.20	1.27	1.34	0.047	0.050	0.053
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
E3	1.89	1.99	2.09	0.074	0.078	0.082
F	0.05	0.12	0.19	0.002	0.005	0.007
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.41	0.51	0.61	0.016	0.020	0.024
K1	0.64	0.74	0.84	0.025	0.029	0.033
K2	0.54	0.64	0.74	0.021	0.025	0.029
W	0.13	0.23	0.33	0.005	0.009	0.013
W1	0.31	0.41	0.51	0.012	0.016	0.020
W2	2.72	2.82	2.92	0.107	0.111	0.115
W3	2.86	2.96	3.06	0.113	0.117	0.120
W4	0.41	0.51	0.61	0.016	0.020	0.024
θ	5°	10°	12°	5°	10°	12°

DWG: 6009

Note

- Millimeters will govern

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8L DUAL ASYMMETRIC



Recommended Minimum Pads
Dimensions in mm [inches]



Disclaimer

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